

描述 / Descriptions

SOT-23 塑封封装 N 沟道 MOS 场效应管。 N- CHANNEL MOSFET in a SOT-23 Plastic Package.

特征 / Features

芯片采用超高密度圆胞设计技术,R_{DS(ON)}导通电阻小,SOT-23 封装。 Super high dense cell design for low R_{DS(ON)},SOT-23 package.

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PIN1: G

PIN 2 : S

PIN 3 : D

用途 / Applications

电池管理,高速开关,低功率 DC-DC 转换。 Battery management, High speed switch, low power DC to DC converter.

印章代码 / Marking

Marking	A2SHB
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极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数	符号	数值	单位
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±8	V
Drain Current – Continuous	I _D	3.0	Α
Pulsed Drain Current	I _{DM}	10	Α
Continuous Source Current	Is	0.95	Α
Power Dissipation	P _D	0.9	W
Storage Temperature Range	T _{stg}	-55∼150	$^{\circ}$

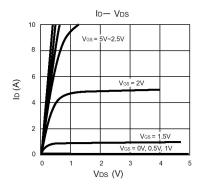


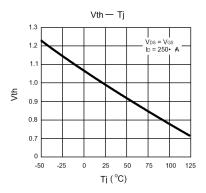
电性能参数 / Electrical Characteristics(Ta=25°C)

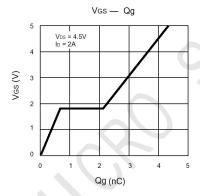
参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain–Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} =0 I_D =10 μ A		20	тур	IVIUX	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0	V _{DS} =20V			1.0	μA
Gate-Body Leakage.	I _{GSS}	V _{GS} =±8V	V _{DS} =0V			±100	nA
Static Drain–Source On–Resistance	R _{DS(on)1}	V _{GS} =4.5V	I _D =3.6A			60	mΩ
	R _{DS(on)2}	V _{GS} =2.5V	I _D =3.1A		X	115	mΩ
Forward Transconductance	g FS	V _{DS} =5V	I _D =3.6A		8		S
Drain–Source Diode Forward Voltage	V _{SD}	V _{GS} =0V	I _D =1.25A		0.75	1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS}	I _D =50μA	0.50		1.0	V
State Drain Current	I _{D(on)}	V _{DS} =5V	V _{GS} =2.5V	4			Α
Turn-On Delay Time	t _{d(on)}		-())		7		
Turn-On Rise Time	t _r	V _{DD} =10V	I _D =3.6A		55		20
Turn-Off Delay Time	t _{d(off)}	V_{GEN} =4.5V R_{GEN} =6 Ω			15		ns
Turn-Off Fall Time	t _f				10		

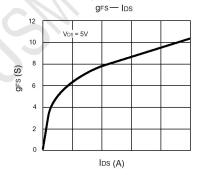


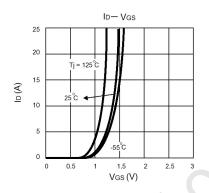
电参数曲线图 / Electrical Characteristic Curve

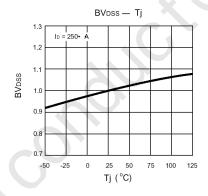


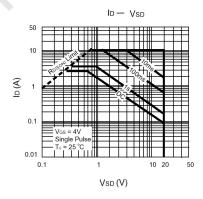


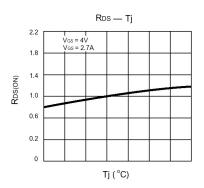










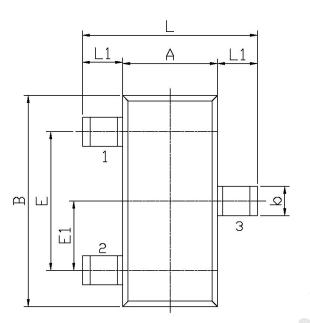


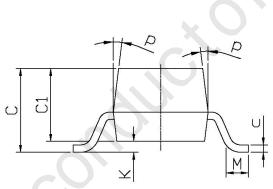


外形尺寸图 / Package Dimensions

S0T-23

单位; mm





Symbol	Dimensions In Millmeters		C. I. I	Dimensions In Millmeters		
	Min	Max	Symbol	Min	Max	
L	ณ	2.7	С	1.30Ma×		
L1	0.45	0.65	C1	0.90	1.20	
Α	1.15	1.50	_	0.05	0.20	
В	2.70	3.10	K	0	0.10	
E	1.70	2.10	M	0.20MIN		
E1	0.85	1.05	Р	7°		
b	0.35	0,55				